

IN THE SPECIFICATION:

Please amend the Specification as follows:

On Page 2, please revise the amended second complete paragraph on this page, and please rewrite by replacing with the following paragraph:

--The invention relates to a semiconductor wafer comprising a substrate wafer made of monocrystalline silicon and an epitaxial layer deposited thereon, which is characterized in that the substrate wafer has a resistivity of from 0.1 to 50  $\Omega\text{cm}$ , an oxygen concentration of less than  $7.5 \times 10^{17} \text{ atcm}^{-3}$ , and a nitrogen concentration of from  $1 \times 10^{13}$  to  $5 \times 10^{15} \text{ atcm}^{-3}$ , and the epitaxial layer has a thickness of from 0.2 to 1.0  $\mu\text{m}$  and has a top surface on which fewer than 30 LLS defects with a size of more than 0.085  $\mu\text{m}$  can be detected.--